

Feature

- Precision MEMS process
- High performance, shielded, Micro-cavity structure
- Silicon substrate, 50Ω CPW output
- Au wire bonding, for MCM applications

Environmental Specifications

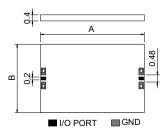
Operating Temperature	-55℃~+85℃	
Storage Temperature	-55℃~+125℃	
Max. Input Power	35dBm	

Electrical Specifications(T_A=+25°C)

Parameter	Min.	Тур.	Max.	Unit
Center Freq. (f₀)	-	11	-	GHz
Pass Band	10	-	12	GHz
Ripple in Pass band	-	-	1	dB
Insertion Loss @ f₀	-	-	1.6	dB
Return Loss	12	-	-	dB
	≥30@9.2GHz&13GHz			dB
Out of band	≥40@8.8	dB		
Attenuation	≥60@DC~8.5GHz			dB
	≥60@14~17GHz			
Group Delay Variation	≤1@10~12GHz			
Linear Phase	≤±6@10	0		

S2P file name: SiMS11_2R1-8D2.s2p

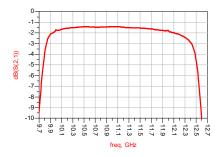
Outline Drawing



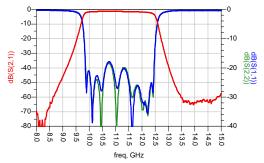
Symbol	Value (mm)			
Syrribor	Min.	Nominal	Max.	
А	7.9	-	8.0	
В	3.9	-	4.0	

Typical Test Curves

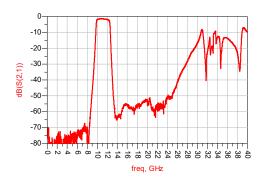
Insertion Loss VS Frequency (T_A=25°C)



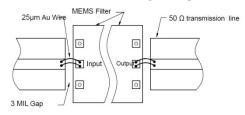
Insertion Loss & Return Loss VS Frequency (T_A=25°C)



Broadband Insertion Loss VS Frequency (T_A=25°C)

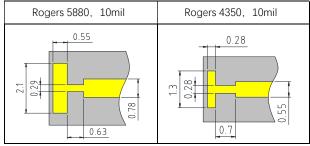


Recommended Assembly Diagrams



Application Notes:

- 1. The chip is back-metalized and can be die mounted with AuSn eutectic performs or with electrically conductive epoxy (for example ME8456).
- 2. The die should be assembled on carriers like Kovar or Mu-Cu which have same Coefficient of thermal expansion. (2.9ppm/ $^{\circ}$ C) with Silicon, thickness 0.2mm max.
- 3. Handle the chips in a clean environment. DO NOT attempt to clean the chip using liquid cleaning systems.
- 4. Handle the chip along the edges with a vacuum collet or with a sharp pair of bent tweezers.
- 5. Recommended to use T structure as below for bonding.



6. If you have any questions, please contact us.